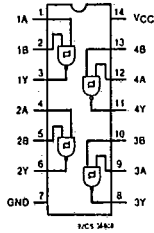


CD54/74HC132
CD54/74HCT132

HARRIS SEMICONDUCTOR . 27E. D ■ 4302271 0017572 3 ■ HAS

High-Speed CMOS Logic

T-51-21-00



Quad 2-Input NAND Schmitt Trigger

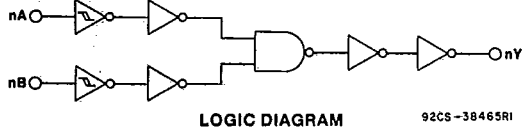
Type Features:

- Unlimited input rise and fall times
- Exceptionally high noise immunity

FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

The RCA-CD54/74HC132 and CD54/74HCT132 each contain four 2-input NAND Schmitt Triggers in one package.

The CD54HC132 and CD54HCT132 are supplied in 14-lead ceramic dual-in-line packages (F suffix). The CD74HC132 and CD74HCT132 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both devices are also available in chip form (H suffix).



LOGIC DIAGRAM

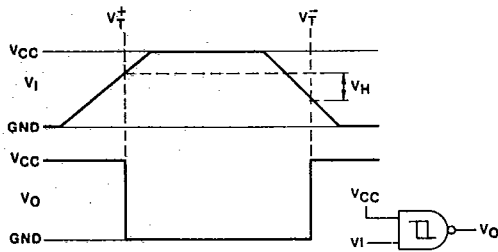
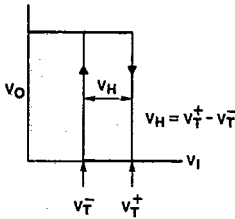


Fig. 1 - Hysteresis definition, characteristic, and test setup.

Family Features:

- Fanout (Over Temperature Range):
Standard Outputs - 10 LSTTL Loads
Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range:
CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:
2 to 6 V Operation
High Noise Immunity:
 $N_{IL} = 37\%$, $N_{IH} = 51\%$ of V_{CC} ; @ $V_{CC} = 5 V$
- CD54HCT/CD74HCT Types:
4.5 to 5.5 V Operation
Direct LSTTL Input Logic Compatibility
 $V_{IL} = 0.8 V$ Max., $V_{IH} = 2 V$ Min.
CMOS Input Compatibility
 $I_L \leq 1 \mu A$ @ V_{OL} , V_{OH}

TRUTH TABLE

INPUTS		OUTPUTS
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

H = High level
L = Low level

CD54/74HC132
CD54/74HCT132

HARRIS SEMICONDUCTOR SECTOR 27E D ■ 4302271 0017573 5 ■ HAS

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V_{CC}):
(Voltages referenced to ground) -0.5 to + 7 V

DC INPUT DIODE CURRENT, I_{IK} (FOR V_i < -0.5 V OR V_i > V_{CC} + 0.5V) ±20mA

DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} + 0.5V) ±20mA

DC DRAIN CURRENT, PER OUTPUT (I_o) (FOR -0.5 V < V_o < V_{CC} + 0.5V) ±25mA

DC V_{CC} OR GROUND CURRENT (I_{CC}) ±50mA

POWER DISSIPATION PER PACKAGE (P_o):

For T_A = -40 to +60°C (PACKAGE TYPE E) 500 mW

For T_A = +60 to +85°C (PACKAGE TYPE E) Derate Linearly at 8 mW/°C to 300 mW

For T_A = -55 to +100°C (PACKAGE TYPE F, H) 500 mW

For T_A = +100 to -125°C (PACKAGE TYPE F, H) Derate Linearly at 8 mW/°C to 300 mW

For T_A = -40 to +70°C (PACKAGE TYPE M) 400 mW

For T_A = +70 to +125°C (PACKAGE TYPE M) Derate Linearly at 6 mW/°C to 70 mW

OPERATING-TEMPERATURE RANGE (T_A):

PACKAGE TYPE F, H -55 to +125°C

PACKAGE TYPE E, M -40 to +85°C

STORAGE TEMPERATURE (T_{stg}) -65 to +150°C

LEAD TEMPERATURE (DURING SOLDERING):

At distance 1/16 ± 1/32 in. (1.59 ± 0.79 mm) from case for 10 s max. +265°C

Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only +300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} .*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _i , V _o	0	V _{CC}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	Unlimited	ns
at 4.5 V	0	Unlimited	ns
at 6 V	0	Unlimited	ns

*Unless otherwise specified, all voltages are referenced to Ground.

HARRIS SEMICONDUCTOR 27E D 430227J 0017574 7 HAS

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CD74HC132/CD54HC132										CD74HCT132/CD54HCT132										UNITS
	TEST CONDITIONS			74HC/54HC TYPE		74HC TYPE		54HC TYPE		TEST CONDITIONS		74HCT/54HCT TYPE		74HCT TYPE		54HCT TYPE					
	V_I	I_O	V_{CC}	+25°C		-40/+85°C		-55/+125°C		V_I	V_{CC}	+25°C		-40/+85°C		-55/+125°C					
	V	mA	V	Min	Max	Min	Max	Min	Max	V	V	Min	Max	Min	Max	Min	Max				
Input Switch Points	V_{T^+}		2	0.7	1.5	0.7	1.5	0.7	1.5			—	—	—	—	—	—	V			
			4.5	1.7	3.15	1.7	3.15	1.7	3.15		4.5	1.2	1.9	1.2	1.9	1.2	1.9				
			6	2.1	4.2	2.1	4.2	2.1	4.2		5.5	1.4	2.1	1.4	2.1	1.4	2.1				
	V_{T^-}		2	0.3	1	0.3	1	0.3	1			—	—	—	—	—	—	V			
			4.5	0.9	2.2	0.9	2.2	0.9	2.2		4.5	0.5	1.2	0.5	1.2	0.5	1.2				
			6	1.2	3	1.2	3	1.2	3		5.5	0.6	1.4	0.6	1.4	0.6	1.4				
V_H		2	0.2	1	0.2	1	0.2	1			—	—	—	—	—	—	V				
		4.5	0.4	1.4	0.4	1.4	0.4	1.4		4.5	0.4	1.4	0.4	1.4	0.4	1.4					
		6	0.6	1.6	0.6	1.6	0.6	1.6		5.5	0.4	1.5	0.4	1.5	0.4	1.5					
High-Level Output Voltage V_{OH}	or	V_{T^-} or V_{T^+}	-0.02	2	1.9	—	1.9	—	1.9	—	V_{T^-} or V_{T^+}	—	—	—	—	—	—	V			
				4.5	4.4	—	4.4	—	4.4	—	4.5	4.4	—	4.4	—	4.4	—				
				6	5.9	—	5.9	—	5.9	—		—	—	—	—	—	—				
TTL Loads	or	V_{T^-} or V_{T^+}	-4	4.5	3.98	—	3.84	—	3.7	—	V_{T^-} or V_{T^+}	4.5	3.98	—	3.84	—	3.7	V			
				—	—	—	—	—	—	—		—	—	—	—	—	—				
				-5.2	6	5.48	—	5.34	—	5.2	—		—	—	—	—	—		—		
Low-Level Output Voltage V_{OL}	or	V_{T^-} or V_{T^+}	0.02	2	—	0.1	—	0.1	—	0.1	V_{T^-} or V_{T^+}	—	—	—	—	—	—	V			
				4.5	—	0.1	—	0.1	—	0.1	—	4.5	—	0.1	—	0.1	—		0.1		
				6	—	0.1	—	0.1	—	0.1	—		—	—	—	—	—		—		
TTL Loads	or	V_{T^-} or V_{T^+}	4	4.5	—	0.26	—	0.33	—	0.4	V_{T^-} or V_{T^+}	4.5	—	0.26	—	0.33	—	0.4	V		
				—	—	—	—	—	—	—		—	—	—	—	—	—	—			
				5.2	6	—	0.26	—	0.33	—	0.4		—	—	—	—	—	—		—	
Input Leakage Current	I_I		6	—	± 0.1	—	± 1	—	± 1	Any Voltage Between V_{CC} and Gnd	5.5	—	± 0.1	—	± 1	—	± 1	μA			
Quiescent Device Current	I_{CC}		0	6	—	2	—	20	—	40	V_{CC} or Gnd	5.5	—	2	—	20	—	40	μA		
Additional Quiescent Device Current per Input Pin: 1 Unit Load ΔI_{CC}^*											$V_{CC}-2.1$	4.5 to 5.5	Min	Typ	Max				μA		
													—	100	360	—	450	—	490		

*For dual-supply systems theoretical worst case ($V_I = 2.4$ V, $V_{CC} = 5.5$ V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS*
nA, nB	0.6

*Unit load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25°C.

CD54/74HC132
CD54/74HCT132

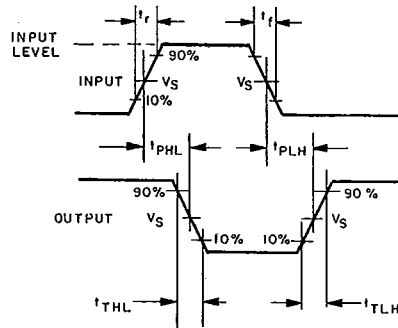
SWITCHING CHARACTERISTICS ($V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$, Input $t_r, t_f = 6\text{ ns}$)

CHARACTERISTIC	C_L (pF)	TYPICAL		UNITS
		HC	HCT	
Propagation Delay A, B to Y	t_{PLH} t_{PHL}	15	13	ns
Power Dissipation Capacitance	C_{PD}^*	—	30	pF

* C_{PD} is used to determine the dynamic power consumption, per gate.
 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where:
 f_i = input frequency
 C_L = output load capacitance
 V_{CC} = supply voltage

SWITCHING CHARACTERISTICS ($C_L = 50\text{ pF}$, Input $t_r, t_f = 6\text{ ns}$)

CHARACTERISTIC	TEST CONDITIONS V_{CC} (V)	+25°C				-40°C to +85°C				-55°C to +125°C				UNITS	
		HC		HCT		74HC		74HCT		54HC		54HCT			
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Propagation Delay A, B to Y	t_{PLH}	—	125	—	—	—	156	—	—	—	188	—	—	ns	
	t_{PHL}	4.5	—	25	—	33	—	31	—	41	—	38	—		50
		6	—	21	—	—	—	27	—	—	—	32	—		—
Output Transition Time	t_{TLH}	2	—	75	—	—	—	95	—	—	—	110	—	—	
	t_{THL}	4.5	—	15	—	15	—	19	—	19	—	22	—	22	
		6	—	13	—	—	—	16	—	—	—	19	—	—	
Input Capacitance	C_i	—	—	10	—	10	—	10	—	10	—	10	—	10	



	54/74HC	54/74HCT
INPUT LEVEL	V_{CC}	3V
V_S	50% V_{CC}	1.3V

92CS-36948R1

Fig. 2 - Transition times and propagation delay times.

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